

## AMENDMENTS TO THE CLAIMS

Claims 1-19. (Canceled)

20. (Original) A CMOS device having FETs with effective channel lengths less than or equal to approximately 0.1  $\mu\text{m}$  formed in adjacent, retrograde nwells and pwells, wherein threshold voltages of FETs formed with approximately 1.5  $\mu\text{m}$  of an interface between said nwells and pwells are constant within approximately 10 mV.
21. (New) The CMOS device of claim 20, wherein p-type dopant regions are located immediately below said retrograde nwells.
22. (New) The CMOS device of claim 20, wherein said retrograde nwells comprise a first n-type dopant region having a first dopant level, a second n-type dopant region immediately above said first n-type dopant region and having a second dopant level, and a third n-type dopant region immediately above said second n-type dopant region and having a third dopant level.
23. (New) The CMOS device of claim 22, wherein the first dopant level is greater than the second dopant level.
24. (New) The CMOS device of claim 23, wherein the second dopant level is greater than the third dopant level.
25. (New) The CMOS device of claim 24 further comprising a p-type dopant region immediately below the first n-type dopant region.
26. (New) The CMOS device of claim 20, wherein said retrograde pwells comprise a first p-

BUR9-2002-0008-US2

type dopant region having a first dopant level, a second p-type dopant region immediately above said first p-type dopant region and having a second dopant level, and a third p-type dopant region immediately above said second p-type dopant region and having a third dopant level.

27. (New) The CMOS device of claim 22, wherein said retrograde wells comprise a first p-type dopant region having a first dopant level, a second p-type dopant region immediately above said first p-type dopant region and having a second dopant level, and a third p-type dopant region immediately above said second p-type dopant region and having a third dopant level.
28. (New) The CMOS device of claim 27, wherein said first p-type dopant region is located substantially adjacent to said first n-type dopant region.